

XBS204S17R-G

查询XBS204S17R-G供应商

ETR1612-002a

Schottky Barrier Diode, 2A, 40V Type

FEATURES

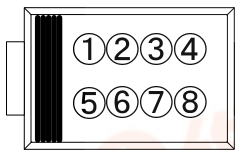
Forward Voltage	: $V_F=0.485V$ (TYP.)
Forward Current	: $I_{F(AVE)}=2A$
Repetitive Peak Reverse Voltage	: $V_{RM}=40V$

ABSOLUTE MAXIMUM RATINGS

$T_a=25^\circ C$

PARAMETER	SYMBOL	RATINGS	UNIT
Repetitive Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage (DC)	V_R	40	V
Forward Current (Average)	$I_{F(AVE)}$	2	A
Non Continuous Forward Surge Current ¹	I_{FSM}	50	A
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature Range	T_{stg}	-55~+150	$^\circ C$

MARKING RULE



①②③④⑤⑥: 204S17(Product Number)
⑦⑧ : Assembly Lot Number

PRODUCT NAME

PRODUCT NAME	DEVICE ORIENTATION
XBS204S17R-G	SMA (Halogen & Antimony free)
XBS204S17R	SMA

* The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

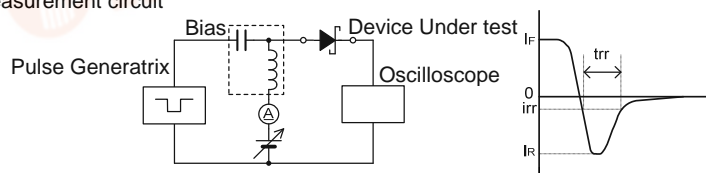
* The device orientation is fixed in its embossed tape pocket.

ELECTRICAL CHARACTERISTICS

$T_a=25^\circ C$

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN.	TYP.	MAX.	
Forward Voltage	V_{F1}	$I_F=200\mu A$	-	0.15	-	V
	V_{F2}	$I_F=2A$	-	0.485	0.54	V
Reverse Current	I_{R1}	$V_R=20V$	-	2.5	-	μA
	I_{R2}	$V_R=40V$	-	6	200	μA
Inter-Terminal Capacity	C_t	$V_R=1V, f=1MHz$	-	180	-	pF
Reverse Recovery Time ^{*2}	t_{rr}	$I_F=I_R=10mA, irr=1mA$	-	51	-	ns

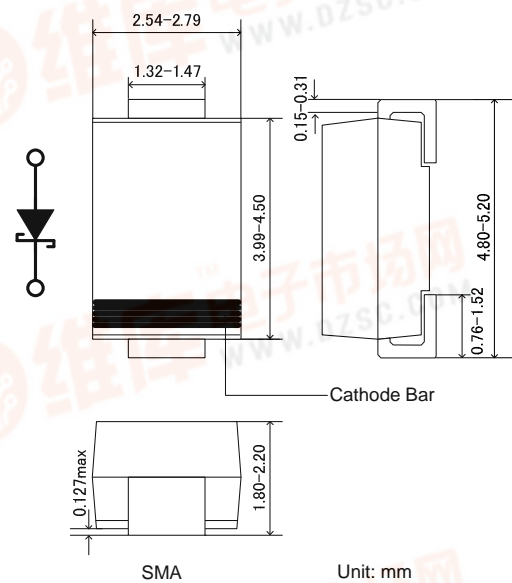
*2 : t_{rr} measurement circuit



APPLICATIONS

- Rectification
- Protection against reverse connection of battery

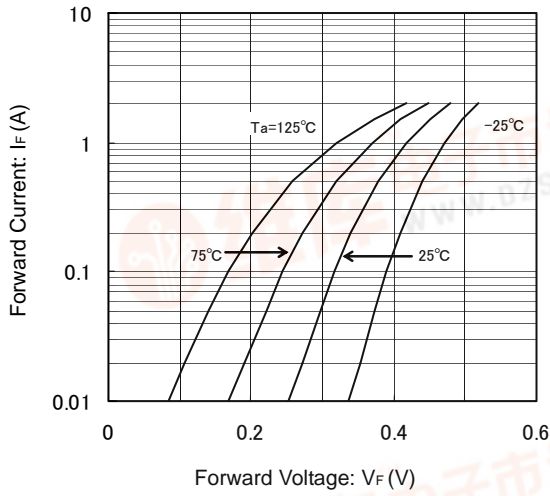
PACKAGING INFORMATION



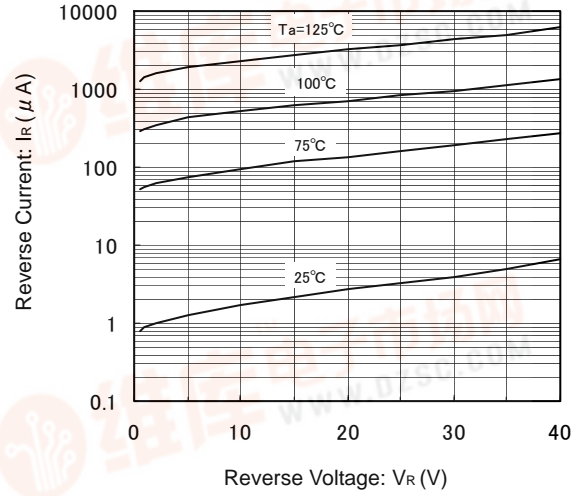
Unit: mm

TYPICAL PERFORMANCE CHARACTERISTICS

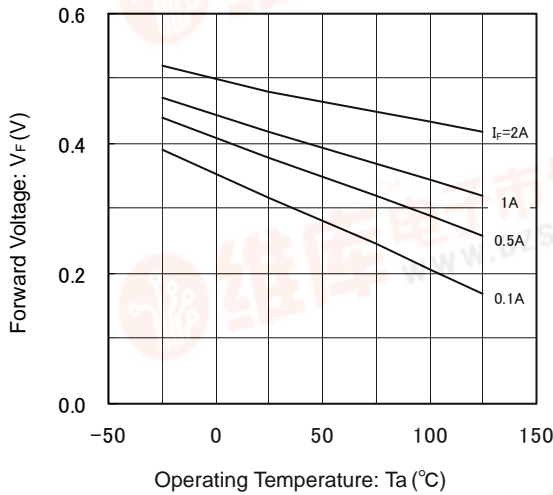
(1) Forward Current vs. Forward Voltage



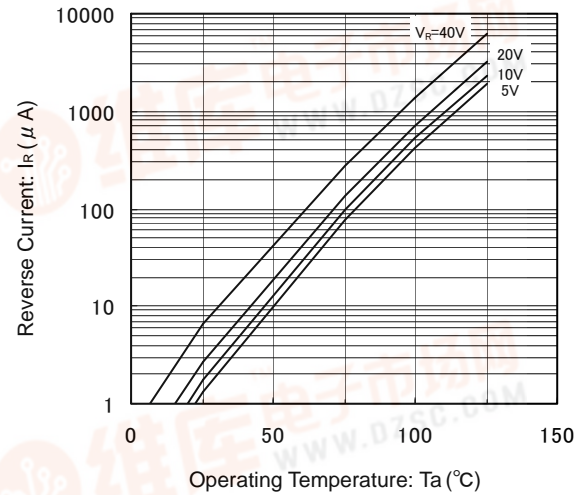
(2) Reverse Current vs. Reverse Voltage



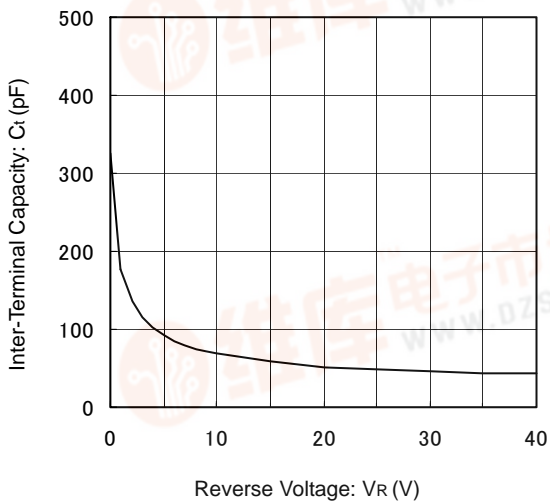
(3) Forward Voltage vs. Operating Temperature



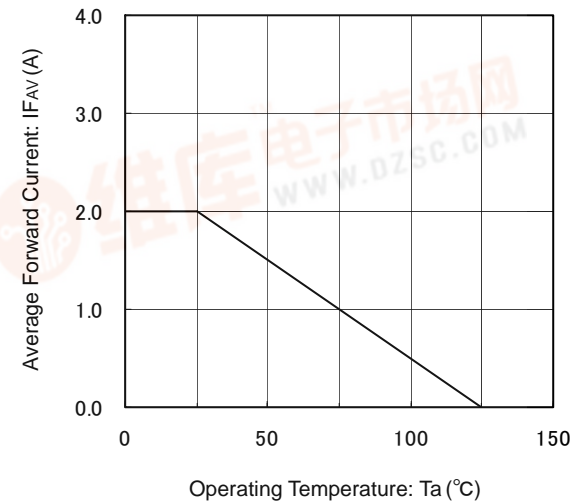
(4) Reverse Current vs. Operating Temperature



(5) Inter-Terminal Capacity vs. Reverse Voltage



(6) Average Forward Current vs. Operating Temperature



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